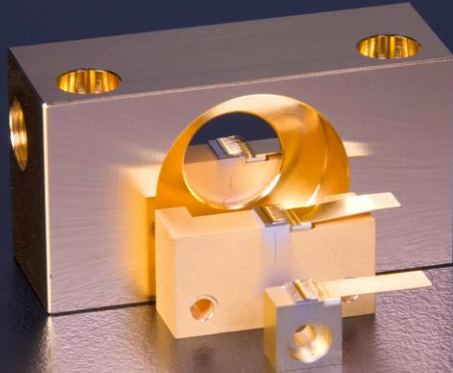


TA-0780-2000

Tapered Amplifier for MOPA Setups



Operation Range: 776 nm to 793 nm

Output Power: 2000 mW

M^2 ($1/e^2$): < 1.7

Side Mode Suppression: > 40 dB

Anti-Reflection Coating: < 0.01%

Packaging: C-Mount / DHP-I / DHP-F

General Description

GaAs based tapered amplifiers are used for the amplification of an existing seed laser. The seed power between 10 mW and 30 mW can be amplified up to nearly diffraction limited power values in the Watt-range. Such a setup is called MOPA (Master Oszillator Power Amplifier). The rear facet and the front facet are both provided with an anti-reflection coating of less than 0.01% to avoid laser action of the amplifier chip itself. Application examples for MOPA setups with tapered amplifiers are optical cooling, optical trapping, Raman spectroscopy and high resolution absorption spectroscopy.

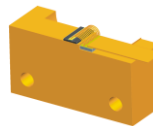
Advantages

- Tuning range between 776 nm and 793 nm
- Suitable for MOPA setups up to 2000mW
- Nearly diffraction limited with M^2 ($1/e^2$) < 1.7
- Side mode suppression of more than 40 dB
- Highly anti-reflection facet coatings < 0.01%
- Passive cooling
- Different packages available

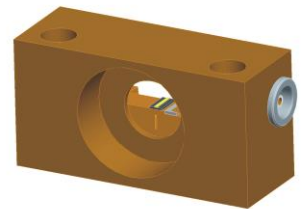
C-Mount



DHP-I



DHP-F



Options

- The TA-0780-2000 can be mounted on a c-mount or optionally on a DHP inset or a DHP frame for better handling.
- The TA-0780-2000 can be ordered with selected beam quality parameters M^2 .
- The TA-0780-2000 is also available for external cavity configurations, see product data sheet TAL-0780-2000.



TA-0780-2000

Specification Data



| Product | | TA-0780-2000 |
|--|----|--------------------------------------|
| Spectral Data | | |
| Wavelength Operation Range ¹ | nm | 776 to 795 |
| Possible Wavelength Operation Without ASE ^{1/2} | nm | 775 to 793 |
| ASE Suppression | dB | > 40 |
| Typical Seed Power ³ | mW | 15 |
| Maximum Seed Power ³ | mW | 30 |
| Minimum Seed Power ³ | mW | 10 |
| Beam Parameter Output Facet | | |
| Output Aperture at Front Side | µm | 256 x 1.2 |
| Divergence Parallel (95%) | ° | 10 to 12 |
| Divergence Perpendicular (95%) | ° | 50 |
| M ² (1/e ²) ⁴ | | < 1.7 |
| Astigmatism | µm | Depends On Operating Conditions |
| Electrical Data | | |
| Typical Operation Current (1000 mW) | A | 2.5 |
| Typical Operation Current (2000 mW) | A | 3.5 |
| Maximum Operation Current With Injection | A | 4.0 |
| Maximum Operation Current Without Injection | A | 2 |
| Operation Voltage | V | < 1.8 |
| Polarization | | TM |
| Thermal Data | | |
| Operating Temperature | °C | 15 to 30 |
| Recommended Heat Sink Temperature | °C | 20 |
| Storage Temperature ⁴ | °C | -20 to 60 |
| Operating Conditions | | Non-Condensing Atmosphere |
| Package | | |
| Heat Sink Type ⁶ | | C-Mount |
| Cavity Length | µm | 4300 |
| Cathode (-) | | Wire Flag |
| Anode (+) | | Base Plate |
| Other Specifications | | |
| RoHS 2002/95EC Compliant | | Yes |
| Optional | | |
| Packaging | | |
| Heat Sink Type | | DHP-inset (DHP-I), DHP-frame (DHP-F) |
| Connector | | Customized Connector Cables |
| Related Products | | |
| For External Cavity Setups | | TAL-0780-2000 |

¹ Tolerance of +/-2nm, not exceeding maximum operation current

² Lower output power possible at periphery areas with max. operation current

³ Measured in front of rear facet

⁴ Measured in accordance to ISO 11146

⁵ In a non condensing atmosphere ⁶ Other heat sinks on request

Safety

This is a laser class IV product according to IEC - Standard International Commission (Publication 825, 1993). The laser light emitted from this laser diode is invisible and/or visible and is harmful to the human eye. The safety regulations for eye and personell protection included in the IEC Standard must be observed to avoid any harm to operating personell. Avoid direct exposure and looking into the laser diode, into the collimated beam or into the fiber when it is linked to the module.

Storage and shipping

Store and ship the diode laser with shortened electrical contacts, in a clean and dry atmosphere and in a tempertaure range of 0°C to 60°C.

Operation and handling

Diode lasers are extremely sensitive to over-voltage. Take extreme precaution to avoid electrostatic charges. Precautions against spiking during switching on and off the power supply must be assured. Correct polarity of power supply must be assured. During handling personell has to wear wrist straps. Grounded work surfaces and additional antistatic techniques are mandatory during handling.

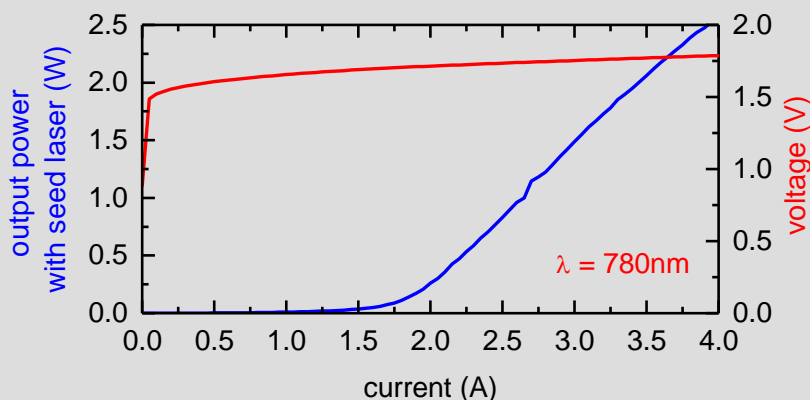
Device failure and safety hazard are caused by operation in excess of maximum ratings.

Exceeding output power and temperature specification will result in accelerated device ageing.

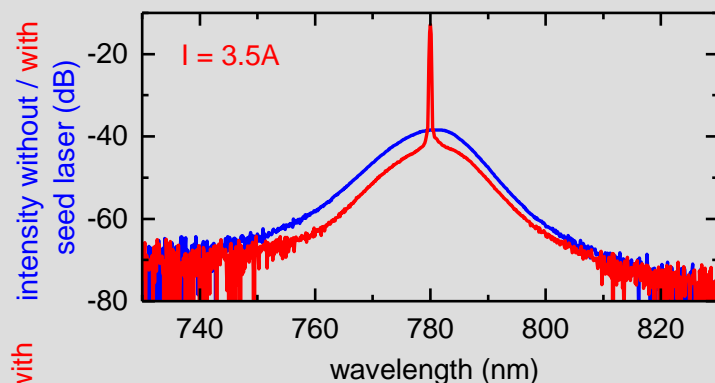
Do not mount via any paste-like media!



The charts presented only describe typical examples. All modules are characterised individually, the results being contained in the documentation included. The display options are subject to alteration.

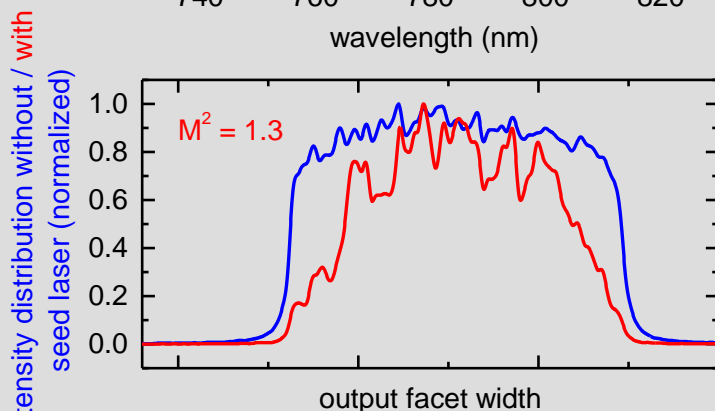


P(I) and U(I) characteristics. All measurements have been done for 20 mW seed power and at 20 °C in cw operation



Amplifier output spectrum without seed power.

Operation beyond the central tuning range and power specified may induce increased thermal stress to the modules and thereby reduce its service life.



Intensity distribution at the amplifier output facet in the slow axis with seed power.

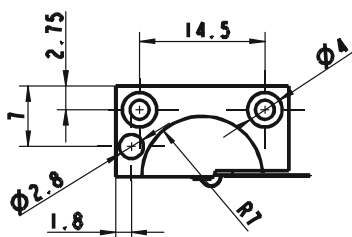
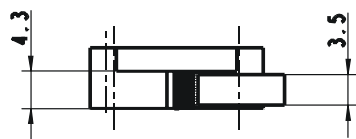
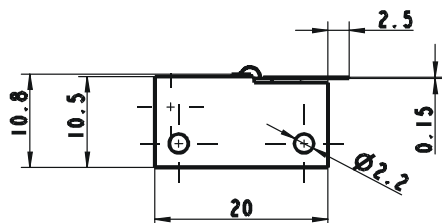
M^2 has been measured using a commercial BeamScope in accordance to ISO 11146.



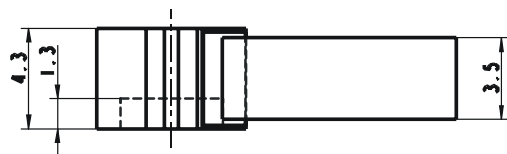
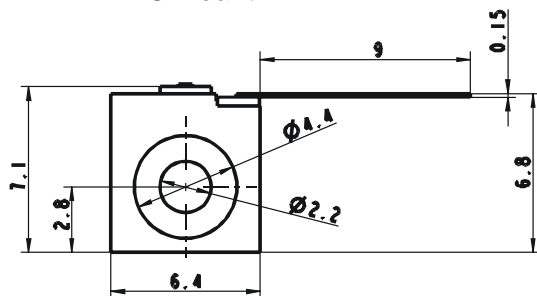
TA-0780-2000

Package Drawings

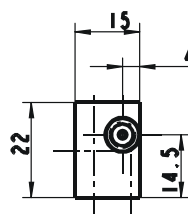
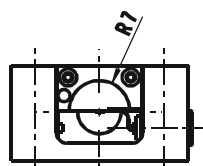
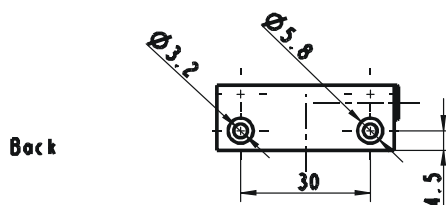
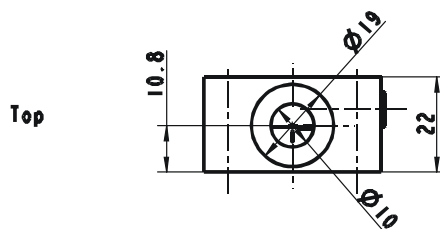
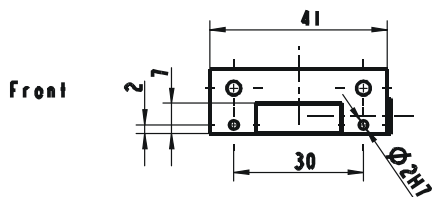
DHP-Inset



C-Mount



DHP-Frame



Bottom

Front

Top

Back

Right

